

=> d his

(FILE 'HOME' ENTERED AT 15:54:59 ON 02 FEB 2007)

FILE 'REGISTRY' ENTERED AT 15:55:10 ON 02 FEB 2007

L1 STRUCTURE UPLOADED

L2 STRUCTURE UPLOADED

L3 1137 S L1 FULL

L4 345 S L2 FULL

FILE 'CAPLUS' ENTERED AT 15:56:04 ON 02 FEB 2007

L5 831 S L3

L6 271 S L4

L7 130239 S BARC OR ARC OR ANTIREFLECTIVE

L8 795 S BARC

L9 0 S (L5 OR L6) AND L8

L10 5 S (L5 OR L6) AND L7

AN 1997:273652 CAPLUS
 DN 126:257062
 TI Fine pattern forming method using photoresist with anti-reflective layer
 IN Oofuji, Takeshi; Nakano, Kaichiro; Maeda, Katsumi
 PA Nippon Electric Co, Japan
 SO Jpn. Kokai Tokkyo Koho, 5 pp.
 CODEN: JKXXAF

DT Patent
 LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 09034118	A	19970207	JP 1995-183756	19950720
PRAI	JP 1995-183756		19950720		

AB The resist, comprising a semiconductor substrate with a processed layer, an anti-reflective layer, and a resist layer containing a resin with transmittance $\geq 70\%$, is exposed and developed to form fine patterns. The resist has large focus depth and gives fine patterns. The resist is useful for lithog. process in production of semiconductor devices.

IT 171439-99-9

RL: TEM (Technical or engineered material use); USES (Uses)
 (fine pattern forming method using photoresist containing polymer with cyclic hydrocarbon group)

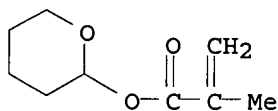
RN 171439-99-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, polymer with octahydro-4,7-methano-1H-inden-5-yl 2-propenoate and tetrahydro-2H-pyran-2-yl 2-methyl-2-propenoate (9CI)
 (CA INDEX NAME)

CM 1

CRN 52858-59-0

CMF C9 H14 O3

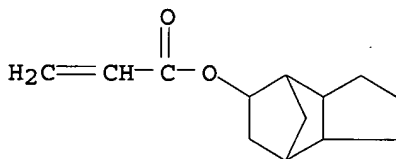


In Resist
Not in ARC

CM 2

CRN 7398-56-3

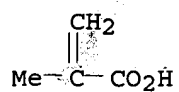
CMF C13 H18 O2



CM 3

CRN 79-41-4

CMF C4 H6 O2



=>